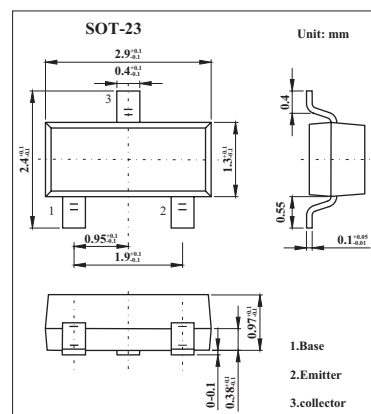


Silicon PNP Epitaxial

2SA1617

■ Features



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-55	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _c	-100	mA
Collector dissipation	P _c	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c = -10μA, I _E = 0	-55			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c = -1mA, R _{BE} = ∞	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _c = 0	-5			V
Collector cutoff current	I _{CBO}	V _{CB} = -30V, I _E = 0			-0.5	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -2V, I _c = 0			-0.5	μA
DC current gain	h _{FE}	V _{CE} = -12V, I _c = -2mA	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = -10mA, I _B = -1mA			-0.2	V
Base-emitter voltage	V _{BE}	V _{CE} = -12V, I _c = -2mA			-0.8	V

■ hFE Classification

Marking	VI	
Rank	B	C
hFE	100~200	160~320